FAIRCHILD

SEMICONDUCTOR®

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FPAB30BH60

Smart Power Module(SPM®) for Front-End Rectifier

General Description

FPAB30BH60 is an advanced smart power module(SPM®) of PFC(Power Factor Correction) that Fairchild has newly developed and designed mainly targeting mid-power application especially for an air conditioners. It combines optimized circuit protection and drive IC matched to high frequency switching IGBTs. System reliability is futher enhanced by the integrated under-voltage lock-out and over-current protection function.

Features

- Low thermal resistance due to Al_2O_3-DBC substrate
- 600V-30A 1-phase IGBT PWM semi-converter including a drive IC for gate driving and protection
- Typical switching frequency of 20kHz
- Isolation rating of 2500Vrms/min.

Applications

- AC 85V ~ 264V single-phase front-end rectifier

Top View

44mm

26.8mm

Bottom View
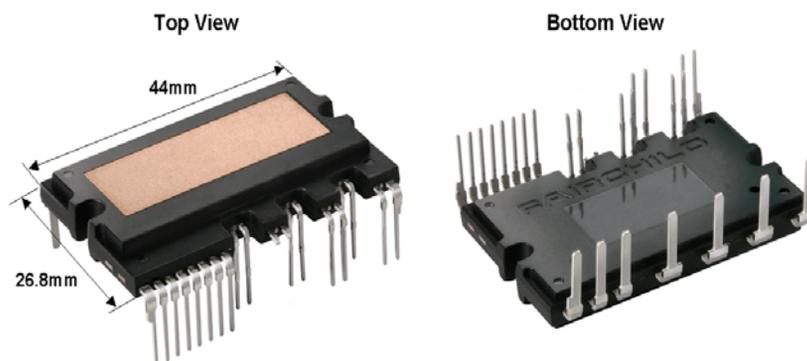
Fig. 1.

Integrated Power Functions

- PFC converter for single-phase AC/DC power conversion (Please refer to Fig. 3)

Integrated Drive, Protection and System Control Functions

- For IGBTs: Gate drive circuit, Overcurrent circuit protection (OC), Control supply circuit under-voltage (UV) protection
- Fault signaling: Corresponding to a UV fault
- Input interface: 5V CMOS/LSTTL compatible, Schmitt trigger input

Pin Configuration

Top View
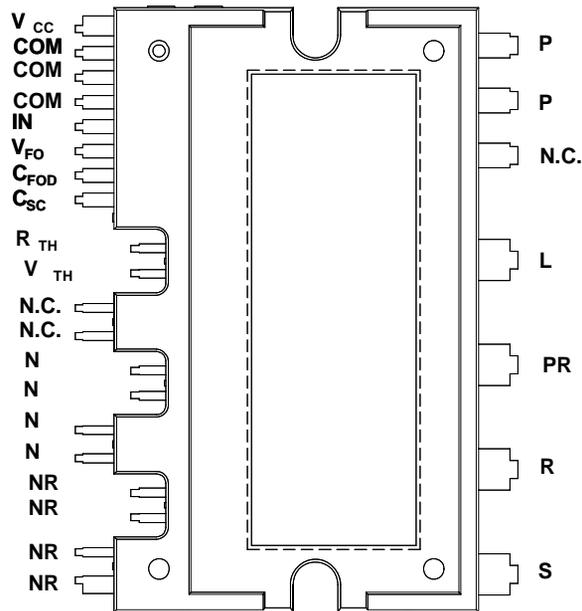
Fig. 2.

Pin Descriptions

Pin Number	Pin Name	Pin Description
1	V_{CC}	Common Bias Voltage for IC and IGBTs Driving
2,3,4	COM	Common Supply Ground
5	$IN_{(R)}$	Signal Input for Low-side R-phase IGBT
6	V_{FO}	Fault Output
7	C_{FOD}	Capacitor for Fault Output Duration Time Selection
8	C_{SC}	Capacitor (Low-pass Filter) for Over Current Detection
9	$R_{(TH)}$	NTC Thermistor terminal
10	$V_{(TH)}$	NTC Thermistor terminal
11,12	N.C	No Connection
13~16	N	IGBT emitter
17~20	N_R	Negative DC-Link of Rectifier
21,22	P	Positive Rail of DC–Link
23	N.C	No Connection
24	L	Reactor connection pin
25	P_R	Positive DC–Link of Rectifier
26	R	AC input for R-phase
27	S	AC input for S-phase

* 11th and 12th pins are cut. Please refer to package outline drawings for more detail.

## Internal Equivalent Circuit and Input/Output Pins
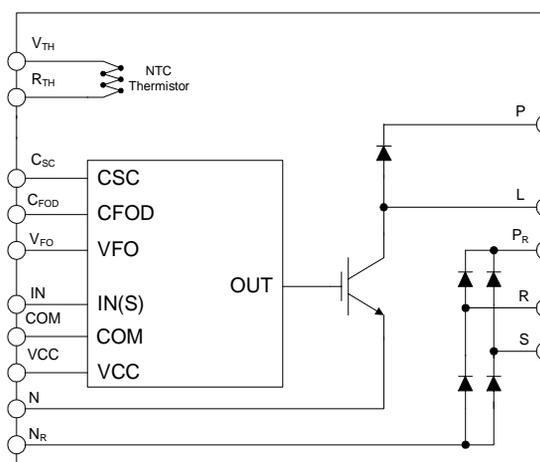
Fig. 3.

Package Marking & Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FPAB30BH60	FPAB30BH60	SPM27-IA	-	-	10

Absolute Maximum Ratings (T_J = 25°C, Unless Otherwise Specified)

Converter Part

Item	Symbol	Condition	Rating	Unit
Supply Voltage	V_i	Applied between R-S	264	V_{RMS}
Supply Voltage (Surge)	$V_{i(Surge)}$	Applied between R-S	500	V
Output Voltage	V_{PN}	Applied between P- N	450	V
Output Voltage (Surge)	$V_{PN(Surge)}$	Applied between P- N	500	V
Collector-emitter Voltage	V_{CES}		600	V
Input Current (100% Load)	I_i	T_C < 95°C, V_i=220V, V_{PN}= 390V, V_{PWM}=20kHz	25	A
Input Current (125% Load)	$I_{i(125\%)}$	T_C < 95°C, V_i=220V, V_{PN}= 390V, V_{PWM}=20kHz, 1min Non-repetitive	30	A
Collector Dissipation	P_C	T_C = 25°C per One IGBT	169	W
Operating Junction Temperature	T_J	(Note 1)	-20 ~ 150	°C

Note
1. The maximum junction temperature rating of the power chips integrated within the SPM® is 150 °C(@T_C ≤ 100°C). However, to insure safe operation of the SPM®, the average junction temperature should be limited to $T_{J(ave)}$ ≤ 125°C (@T_C ≤ 100°C)

Control Part

Item	Symbol	Condition	Rating	Unit
Control Supply Voltage	V_{CC}	Applied between V_{CC} - COM	20	V
Input Signal Voltage	V_{IN}	Applied between IN - COM	-0.3~5.5	V
Fault Output Supply Voltage	V_{FO}	Applied between V_{FO} - COM	-0.3~V_{CC}+0.3	V
Fault Output Current	I_{FO}	Sink Current at V_{FO} Pin	5	mA
Current Sensing Input Voltage	V_{SC}	Applied between C_{SC} - COM	-0.3~V_{CC}+0.3	V

Total System

Item	Symbol	Condition	Rating	Unit
Module Case Operation Temperature	T_C		-20 ~ 100	°C
Storage Temperature	T_{STG}		-40 ~ 125	°C
Isolation Voltage	V_{ISO}	60Hz, Sinusoidal, AC 1 minute, Connection Pins to DBC	2500	V_{rms}

Thermal Resistance

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Junction to Case Thermal Resistance (Referenced to PKG center)	$R_{\theta(j-c)Q}$	IGBT	-	-	0.74	°C/W
	$R_{\theta(j-c)F}$	FRD	-	-	1.44	°C/W
	$R_{\theta(j-c)R}$	Rectifier	-	-	2.07	°C/W

Note :
2. For the measurement point of case temperature(T_C), please refer to Fig. 2.

Electrical Characteristics (T_J = 25°C, Unless Otherwise Specified)

Converter Part

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
IGBT saturation voltage	$V_{CE(sat)}$	V_{CC} =15V, V_{IN} = 5V; I_C =30A	-	2.0	2.8	V
FRD forward voltage	V_{FF}	I_F = 30A	-	1.8	2.5	V
Rectifier forward voltage	V_{FR}	I_F = 30A	-	1.2	1.5	V
Peak surge current	I_{FSM}	Non-repetitive, 60Hz single half-sine wave	200	-	-	A
Switching Times	t_{ON}	V_{PN} = 400V, V_{CC} = 15V, I_C =30A	-	650	-	ns
	$t_{C(ON)}$	V_{IN} = 0V ↔ 5V, Inductive Load	-	400	-	ns
	t_{OFF}	(Note 3)	-	620	-	ns
	$t_{C(OFF)}$		-	200	-	ns
	t_{rr}		-	60	-	ns
	I_{rr}		-	3.5	-	A
Collector - emitter Leakage Current	I_{CES}	V_{CE} = V_{CES}	-	-	250	μA

Note
3. t_{ON} and t_{OFF} include the propagation delay time of the internal drive IC. $t_{C(ON)}$ and $t_{C(OFF)}$ are the switching time of IGBT itself under the given gate driving condition internally. For the detailed information, please see Fig. 4

Control Part

Item	Symbol	Condition		Min.	Typ.	Max.	Unit
Quiescent V_{CC} Supply Current	I_{QCCL}	V_{CC} = 15V, IN = 0V	V_{CC} - COM	-	-	26	mA
Fault Output Voltage	V_{FOH}	V_{SC} = 0V, V_{FO} Circuit: 4.7kΩ to 5V Pull-up		4.5	-	-	V
	V_{FOL}	V_{SC} = 1V, V_{FO} Circuit: 4.7kΩ to 5V Pull-up		-	-	0.8	V
Over Current Trip Level	$V_{SC(ref)}$	V_{CC} = 15V		0.45	0.5	0.55	V
Supply Circuit Under-Voltage Protection	UV_{CCD}	Detection Level		10.7	11.9	13.0	V
	UV_{CCR}	Reset Level		11.2	12.4	13.2	V
Fault-out Pulse Width	t_{FOD}	C_{FOD} = 33nF (Note 4)		1.4	1.8	2.0	ms
ON Threshold Voltage	$V_{IN(ON)}$	Applied between IN - COM		3.0	-	-	V
OFF Threshold Voltage	$V_{IN(OFF)}$			-	-	0.8	V
Resistance of Thermistor	R_{TH}	@ T_C = 25°C (Note Fig. 9)		-	50	-	kΩ
		@ T_C = 100°C (Note Fig. 9)		-	2.99	-	kΩ

Note
4. The fault-out pulse width t_{FOD} depends on the capacitance value of C_{FOD} according to the following approximate equation : $C_{FOD} = 18.3 \times 10^{-6} \times t_{FOD}[F]$

Electrical Characteristics

(a) Turn-on   **(b) Turn-off**
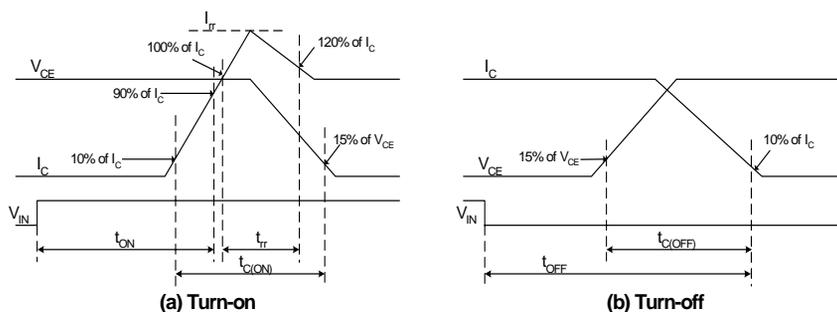
Fig. 4. Switching Time Definition

Mechanical Characteristics and Ratings

Item	Condition		Limits			Units
			Min.	Typ.	Max.	
Mounting Torque	Mounting Screw: - M3	Recommended 0.62N•m	0.51	0.62	0.72	N•m
Device Flatness	Note Fig. 5		0	-	+120	μm
Weight			-	15.00	-	g
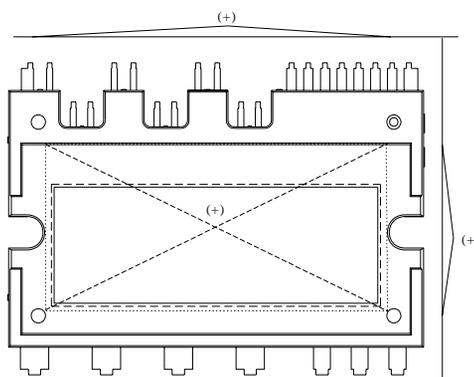
Fig. 5. Flatness Measurement Position

Time Charts of SPMs Protective Function

Input Signal

Internal IGBT
Gate-Emitter Voltage

P 3

Control Supply Voltage

P 5

UV
reset

UV
detect

P 2

Output Current

P 1

P 6

Fault Output Signal

P 4
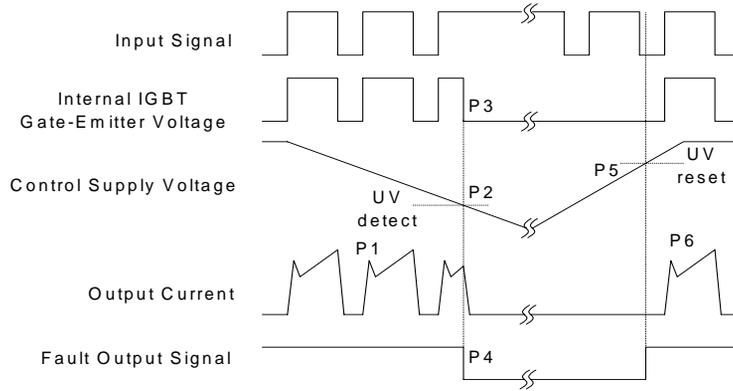
P1 : Normal operation - IGBT ON and conducting current
P2 : Under voltage detection
P3 : IGBT gate interrupt
P4 : Fault signal generation
P5 : Under voltage reset
P6 : Normal operation - IGBT ON and conducting current

Fig. 6. Under-Voltage Protection

Input Signal

P 5

Internal IGBT
Gate-Emitter Voltage

P 6

OC Detection →

Output Current

P 1

P 4

P 7

Sensing Voltage

P 2

OC Reference
Voltage (0.5V)

RC Filter Delay

Fault Output Signal

P 3

P 8
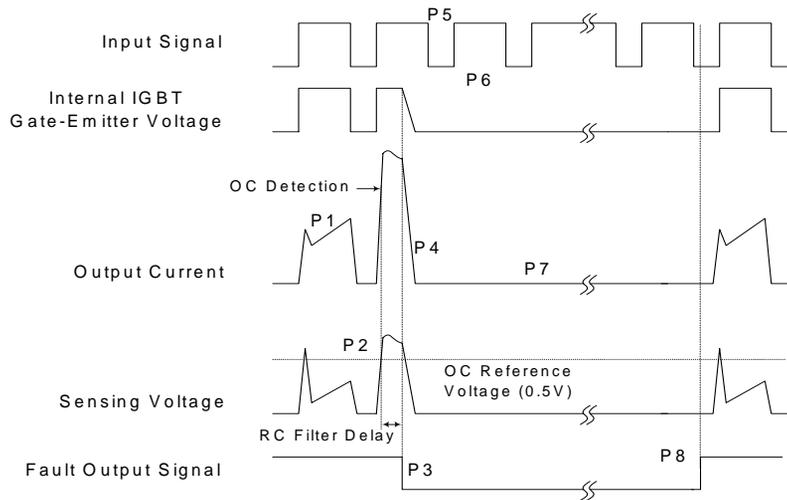
P1 : Normal operation - IGBT ON and conducting current
P2 : Over current detection
P3 : IGBT gate interrupt / Fault signal generation
P4 : IGBT is slowly turned off
P5 : IGBT OFF signal
P6 : IGBT ON signal - but IGBT cannot be turned on during the fault Output activation
P7 : IGBT OFF state
P8 : Fault Output reset and normal operation start

**Fig. 7. Over Current Protection**
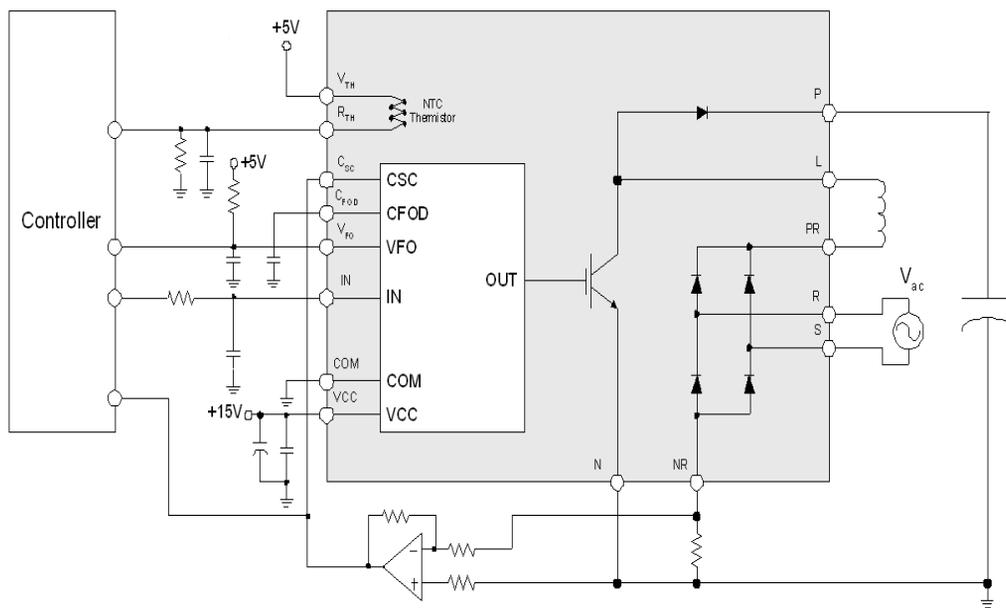
Fig. 8. Application Example

R-T Graph
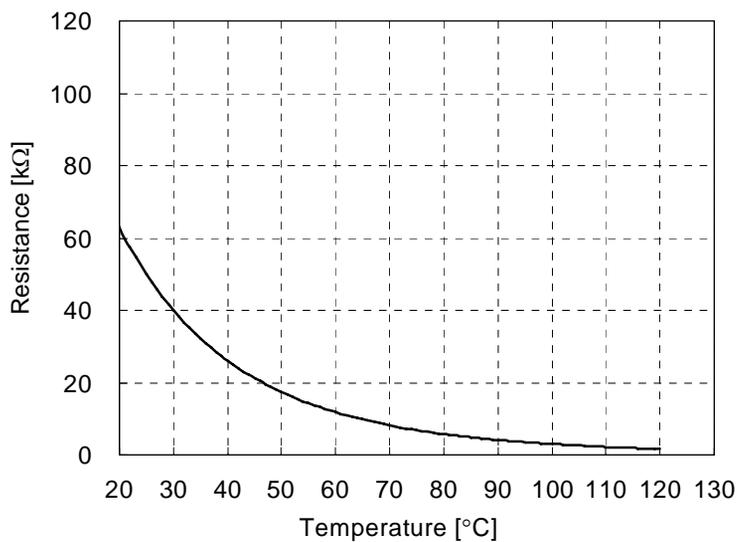
Fig. 9. R-T Curve of the Built-in Thermistor

Detailed Package Outline Drawings

B C A C B C A C B C A A A A A A A A A A

0.70   0.70

Package Center

Lead Pitch : ±0.30
A : 1.778
B : 2.050
C : 2.531

Package Center

NO 20   NO 1

R1.65

Package Center

NO 27

40.00±0.15

44.00

26.80

12.00±0.15

3.10

1.30

20.00

0.50

3~5°

5.50

7.90

13.40

2x4.0±0.30=8.00

4x7.62±0.30=30.48

Package Center

(1.90)

(3.60)

0.70   0.70

1.50

7.00

4-0.80   3-0.80

4-1.30   3-1.30

4-Max3.20   3-Max2.00

Detailed Package Outline Drawings

30.60

26.50

13.4

7.9

R0.70

R0.70

Package Center

11.90±0.30

27.90±0.30

4.10±0.30

Lead Forming Dimension

Package Center

(2.306)

(1.553)

19.694±0.30

20.447±0.30

Package Center

(2.76)

(2.76)

19.24±0.30

19.24±0.30

PKG Center to Lead Distance

Detailed Package Outline Drawings

DETAIL LEAD

LEAD TYPE 2

LEAD TYPE 3   LEAD TYPE 1

3.90±0.20

0.50±0.10   0.50±0.10   0.50±0.10

X   X'

MAX1.20   MAX0.70   MAX0.85
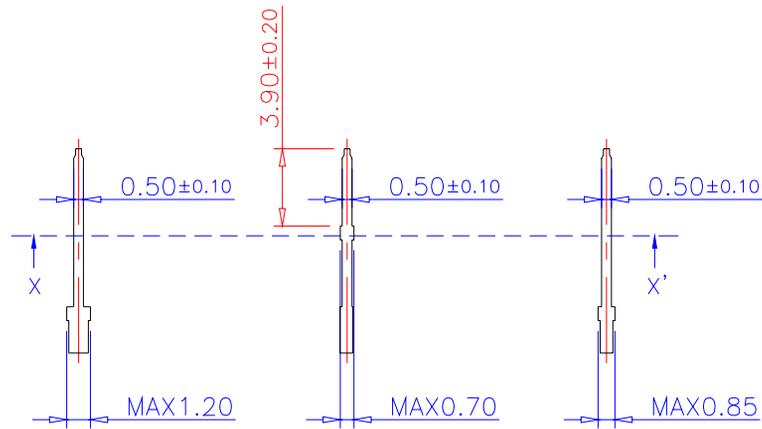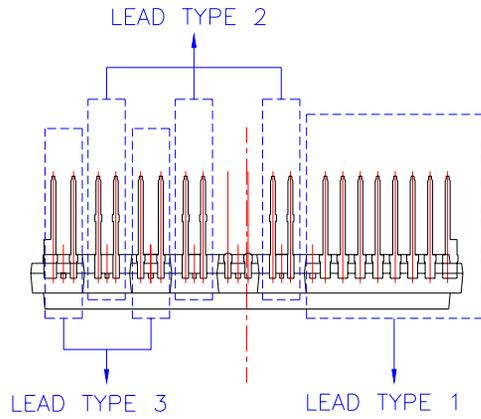
LEAD TYPE 1   LEAD TYPE 2   LEAD TYPE 3

SCALE 2 : 1

0.50   0.70   0.50

0.50   0.50   0.50
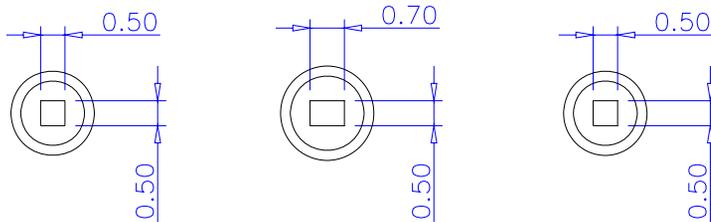
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FPS™	POP™	SuperSOT™-6	
FRFET®	Power220®	SuperSOT™-8	

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